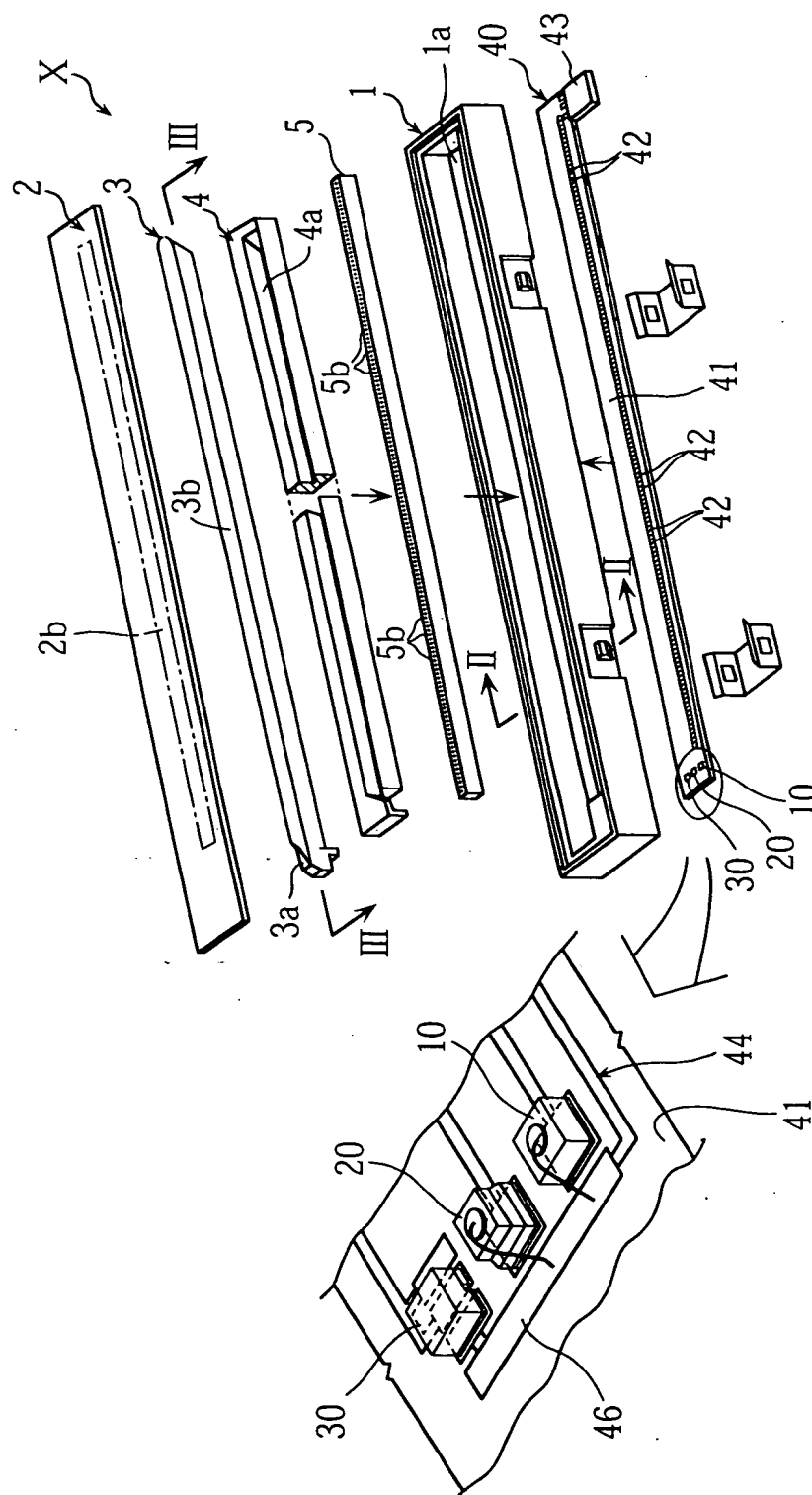


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FIG. 1



A cross-sectional view of a light emitting device 3. The device consists of a substrate 10, a light emitting layer 20, and a protective layer 30. The protective layer 30 is divided into a main body 3b and a curved portion 3a. The main body 3b has a flat top surface 132B and a bottom surface 135 with four notches 139. The curved portion 3a has a curved top surface 133 and a bottom surface 134 with a notch 131. A light emitting layer 136 is located between the substrate 10 and the protective layer 30. Arrows indicate light emission from the light emitting layer 136 through the protective layer 30.

FIG.4A

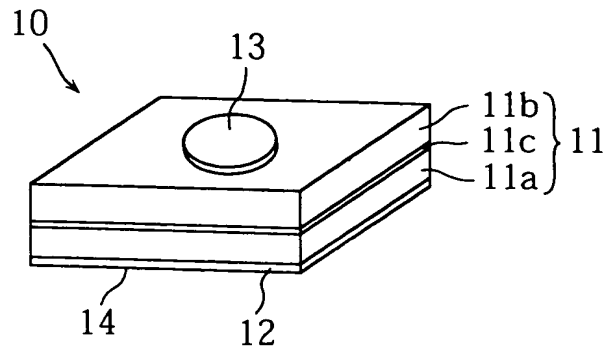


FIG.4B

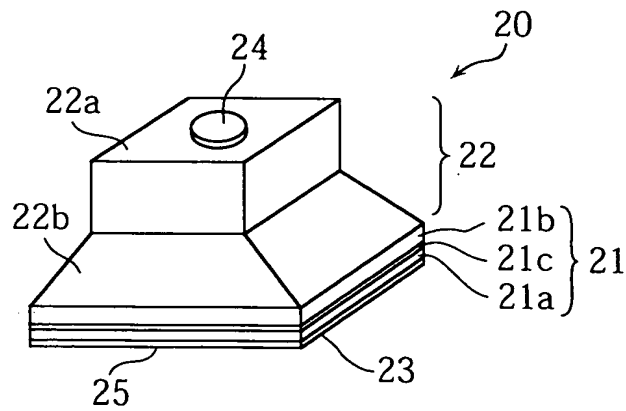


FIG.4C

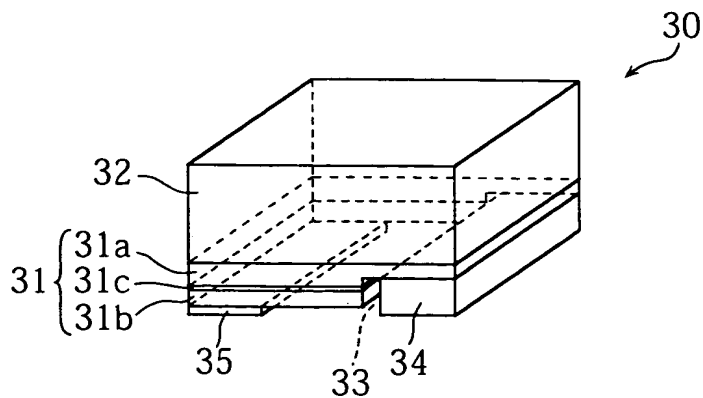


FIG. 5

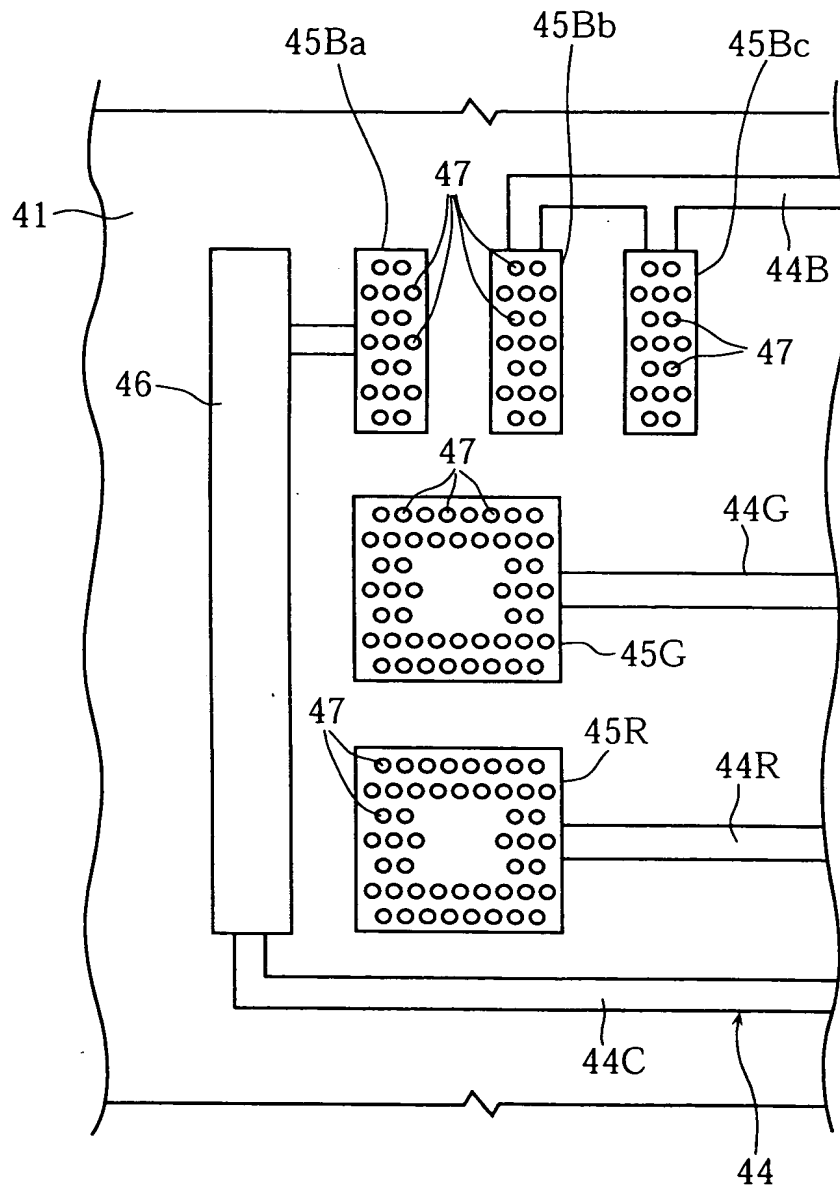


Fig. 1 is a cross-sectional view of a first embodiment of a semiconductor device. The device is mounted on a substrate 41. It includes a base layer 7, a thin layer 46, a patterned layer 47, and a series of layers 7a, 7b, 7c, and 7d. A central component 20(70) is connected to a wire 74. A wire 7 is also shown on the left.

FIG. 10A
PRIOR ART

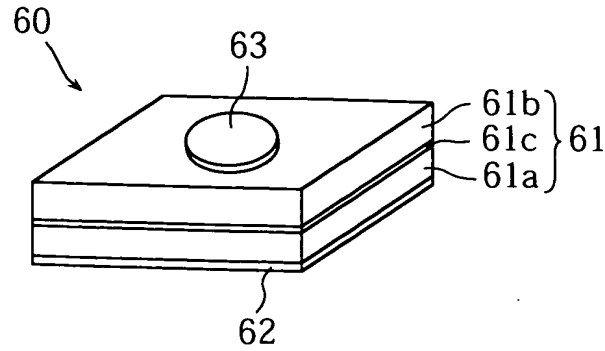


FIG. 10B
PRIOR ART

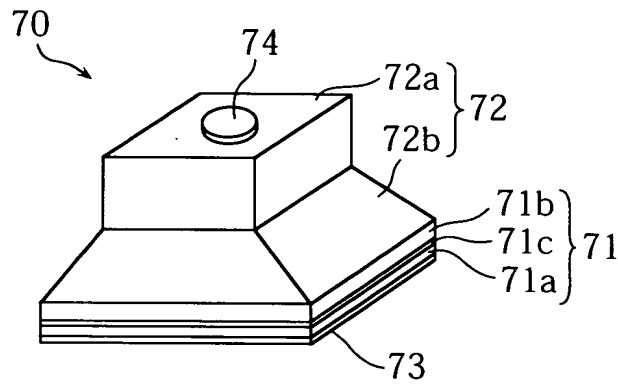


FIG. 10C
PRIOR ART

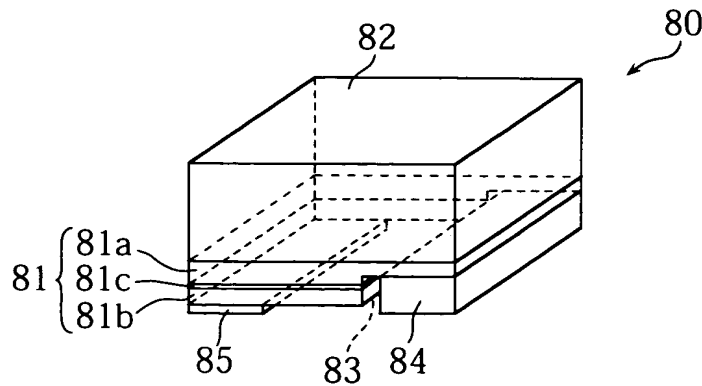


FIG. 11
PRIOR ART

